

Amorphous thin film energy storage

As optimal harvesting outcomes with poling, an output voltage of 38.7 V, power of 413 mW, and power density of 2.8 × 10 6 mW cm -3 were attained for nearly stoichiometric amorphous thin films processed with the highest oxygen pressure.

Here, by structure evolution between fluorite HfO2 and perovskite hafnate, we create an amorphous hafnium-based oxide that exhibits the energy density of ~155 J/cm3 with an efficiency of 87% ...

Finally, the optimized energy-storage performance is achieved in 0.92BT-0.08BMZ thin films annealed at 600 °C, with a large energy density of 55.2 J/cm 3 and a high ...

Low-temperature amorphous thin films with excellent energy storage properties play a crucial role in silicon-based microelectronic applications. The (1-x)Sr0.925Bi0.05TiO3 ...

However, the energy density of these dielectric films remains a critical limitation due to the inherent negative correlation between their maximum polarization (Pmax) and breakdown strength (Eb). This study demonstrates enhanced energy storage performance in multilayer films featuring an ultra-thin layer structure.

Traditional methods to incorporate polycrystalline thin film into flexible systems are often complicated and limited by their sizes. Here, the authors introduce flexible amorphous thin film energy harvester, based on perovskite oxides, on a plastic substrate for electromechanical energy harvesting.

The energy-harvesting performance was excellent despite the amorphous nature of the thin films; peak output values of ~38.7 V, ~413 mW, and ~2.8 × 10 6 mW cm -3 which are the record-high values among reported energy-harvesting devices based on typical polycrystalline-oxide-thin-film cantilevers utilizing mechanical vibrations.

Investigations on the electric performance of these thin film materials present that Bi 3+ ions with a special electronic structure enhance the polarization of amorphous materials; simultaneously, ...

Amorphous films have excellent breakdown strength and energy storage efficiency, and have broad application prospects in dielectric film capacitors. However, its low ...

Finally, the optimized energy-storage performance is achieved in 0.92BT-0.08BMZ thin films annealed at 600 °C, with a large energy density of 55.2 J/cm and a high energy efficiency of 83.6%, demonstrating the great application potential of 0.92BT-0.08BMZ thin films for portable pulse capacitors.

All films were identified as amorphous in the patterns, which only exhibit peaks corresponding to the Pt electrode, irrespective of the oxygen partial pressure. Note that the crystallization of the sputtered CCTO thin films typically requires an annealing temperature of approximately 600 °C 32, 40.



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